



#19/C

520.37546X00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

11/20/02
Smith

Applicants: TORII et al.
Serial No.: 09/391,250
Filed: September 7, 1999
For: MEMORY STRUCTURE WITH A FERROELECTRIC
CAPACITOR AND A FABRICATION METHOD
THEREOF
(As amended)
Group: 2811
Examiner: C. Nguyen

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AMENDMENT-SUBMISSION WITH RCE

Assistant Commissioner
for Patents
Washington, D.C. 20231

November 12, 2002

Sir:

In accordance with the provisions of 37 C.F.R. 1.114, permitting submission of an Amendment with the filing of a RCE, applicants hereby respectfully request entry of the following amendment, noting that a Petition for Extension of Time is being filed herewith for extending the time for filing of the RCE with the present amendment:

IN THE CLAIMS:

Please amend claims 1, 7 and 14 as follows:

1. (Amended) A semiconductor device comprising:

an insulating film formed on a substrate provided with a transistor and having an opening portion;
a conductive film formed in the opening portion; and

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